

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L15	230	257/46.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L16	453	257/104.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L17	517	257/173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L18	355	257/544.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L19	372	257/546.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L20	501	257/653.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L21	1725	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:04
L22	3724	L15 L16 L17 L18 L19 L20 L21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24

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L23	729	22 and anode and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
L24	86036	(semiconductor or ic or die or chip or (integrated adj circuit)) and anode and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:05
L25	2899	L24 and ((n near3 well) or n-well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:06
L26	2899	L24 and ((n near3 well) or n-well or (n-type near2 well))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:06
L27	23160	L24 and (conductivity or dopant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:07
L28	1250	L27 and ((n near2 well) or n-well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:07
L29	812	L28 and (p near2 substrate or (p-type near2 substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 16:07
L30	2899	26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 16:07

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L31	1387	26 and (p near2 substrate or (p-type near2 substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 16:08
L32	1134	31 not 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 16:41
L33	1	("6563181").PN.	USPAT	OR	OFF	2006/03/01 16:41
L34	1	("6521951").PN.	USPAT	OR	OFF	2006/03/01 16:41
L35	1	("6266222").PN.	USPAT	OR	OFF	2006/03/01 16:41
L36	1	("6097078").PN.	USPAT	OR	OFF	2006/03/01 16:42
L37	1	("5905679").PN.	USPAT	OR	OFF	2006/03/01 16:42
L38	1	("5796147").PN.	USPAT	OR	OFF	2006/03/01 16:42
L39	1	("6329694").PN.	USPAT	OR	OFF	2006/03/01 16:42
L40	1	("20030080804").PN.	US-PGPUB; USPAT	OR	OFF	2006/03/01 16:42
L41	8	33 34 35 36 37 38 39 40	US-PGPUB; USPAT	OR	OFF	2006/03/01 16:42
S1	81225	(semiconductor or ic or die or chip or (integrated adj circuit)) and anode and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/01 14:51
S2	21273	S1 and (conductivity or dopant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/01 14:52
S3	1131	S2 and ((n near2 well) or n-well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/01 14:52
S4	683	S3 and (p near2 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:22

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S5	1607	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:51
S6	1	("6563181").PN.	USPAT	OR	OFF	2005/07/06 12:22
S7	223	257/46.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:50
S9	443	257/104.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:50
S10	496	257/173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:50
S11	348	257/544.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:50
S12	367	257/546.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:50
S13	496	257/653.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:50
S14	1612	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:51

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S15	3574	S7 S9 S10 S11 S12 S13 S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 15:24
S16	81339	(semiconductor or ic or die or chip or (integrated adj circuit)) and anode and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:51
S17	21309	S16 and (conductivity or dopant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:51
S18	1135	S17 and ((n near2 well) or n-well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:05
S19	686	S18 and (p near2 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 16:07
S20	3411	S15 not S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:52
S21	572	S20 and anode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/07 15:52
S22	1	("6329694").PN.	USPAT	OR	OFF	2005/07/07 17:24
S23	1	("6266222").PN.	USPAT	OR	OFF	2005/07/07 17:24
S24	1	("6309921").PN.	USPAT	OR	OFF	2005/07/07 17:24
S25	1	("6242793").PN.	USPAT	OR	OFF	2005/07/07 17:24
S26	1	("6218704").PN.	USPAT	OR	OFF	2005/07/07 17:24
S27	1	("5939767").PN.	USPAT	OR	OFF	2005/07/07 17:25

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S28	1	("5882967").PN.	USPAT	OR	OFF	2005/07/07 17:25
S29	1	("5821572").PN.	USPAT	OR	OFF	2005/07/07 17:25
S30	1	("5776807").PN.	USPAT	OR	OFF	2005/07/07 17:25
S31	9	S22 S23 S24 S25 S26 S27 S28 S29 S30	USPAT	OR	OFF	2005/07/07 17:25